

Angular Dependence of the High-Magnetic-Field Phase Diagram of URu₂Si₂

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We present measurements of the magnetoresistivity ρ_{xx} of URu₂Si₂ single crystals in high magnetic fields up to 60 T and at temperatures from 1.4 K to 40 K. Different orientations of the magnetic field have been investigated permitting to follow the dependence on θ of all magnetic phase transitions and crossovers, where θ is the angle between the magnetic field and the easy-axis \mathbf{c} . We find out that all magnetic transitions and crossovers follow a simple $1/\cos\theta$ -law, indicating that they are controlled by the projection of the field on the \mathbf{c} -axis.

KEYWORDS: URu₂Si₂, magnetoresistivity, angular dependence, field-temperature-phase diagram

1. Introduction

URu₂Si₂ is one of the most recently studied heavy-fermion compounds [1]. It exhibits the so-called "hidden-order" state below $T_0 = 17.5$ K [2–6], for which the order parameter is still not identified, and has a transition to superconductivity at 1.5 K [3,4]. The resistivity [7] and magnetic susceptibility [2, 8] of URu₂Si₂ are strongly anisotropic, i.e., angle-dependent. The upper critical field H_{c2} related to the destruction of the superconductivity is also strongly angle-dependent [9]. Under pressure a quantum phase transition leads to an antiferromagnetic ground state [6,10,11]. A magnetic field \mathbf{H} parallel to the easy-axis \mathbf{c} induces a cascade of low-temperature magnetic phase transitions between 35 T and 39 T from the "hidden-order" state to a polarized paramagnetic state. In the last 10 years, the H - T -phase diagram for $\mathbf{H} \parallel \mathbf{c}$ has been investigated by magnetization [12], ultrasound [13], and resistivity [14] measurements. The angle-dependent behavior of the low-temperature quantum phase transitions H_1 , H_2 and H_3 (see Figure 1) at 1.5 K and up to 45 T is also known from magnetization [15] and magnetoresistivity [16] measurements: H_1 , H_2 and H_3 follow a simple $1/\cos\theta$ -law, where θ is the angle between the magnetic field and the \mathbf{c} -axis. Other angle-dependent measurements focused on the study of quantum oscillations [9, 17–20] at lower fields, i.e. inside the hidden-order phase, in order to investigate the Fermi surface. We present here a study of the angle-dependence of the magnetoresistivity of URu₂Si₂ in a larger experimental window, in high magnetic fields up to 60 T and temperatures up to 40 K. The complete H - T -phase diagram is investigated, including all transition and crossover lines.

2. Experimental details

The high-quality single crystals of URu₂Si₂ studied here have been grown by the Czochralski technique. All experiments were done in a ⁴He-cryostat and at ambient pressure. We

have measured the electrical resistivity ρ_{xx} ($\mathbf{I}, \mathbf{U} \parallel \mathbf{a}$, where I and U are the current and voltage, respectively) as a function of the magnetic field using the four-contact method. The high quality of our URu₂Si₂ single crystals is shown by their residual resistivity ratio $\text{RRR} = \rho_{xx}(300\text{K})/\rho_{xx}(2\text{K})$, where ρ_{xx} is the zero-field resistivity. The RRR are 90 for sample #1 and 225 for sample #2. Measurements have been done in 6mm-bore and 17mm-bore 60-T magnets of the LNCMI-T facility with a duration of the pulse of 150 ms and 300 ms, respectively. Sample #1 has been measured in the configurations [$\mathbf{H} \parallel \mathbf{c}$; $\mathbf{I}, \mathbf{U} \parallel \mathbf{a}$] and [$(\mathbf{H}, \mathbf{c}) = 20^\circ$; $\mathbf{I}, \mathbf{U} \parallel \mathbf{a}$]. Sample #2 has been measured in a rotational probe permitting \mathbf{H} to turn in the \mathbf{a} - \mathbf{c} -plane from transversal [$\mathbf{H} \perp \mathbf{I}, \mathbf{a}$; $\theta = 0^\circ$] to longitudinal [$\mathbf{H} \parallel \mathbf{I}, \mathbf{a}$; $\theta = (\mathbf{H}, \mathbf{c}) = 90^\circ$] configurations.

3. Results

Figure 1 (a) presents the resistivity ρ_{xx} of sample #1 as a function of the magnetic field $\mathbf{H} \parallel \mathbf{c}$ for different temperatures T from 1.4 K to 40 K. Above 5 K the magnetoresistivity shows a phase transition at the field H_0 , which is related to the destruction of the "hidden-order" phase, and a broad maximum at the field $H_{\rho,max}$, which is related to a high-temperature crossover, presumably controlled by the destabilization of intersite electronic correlations [21]. H_0 is defined at the extremum of $\partial\rho_{xx}/\partial H$ and vanishes at 17 K, reaching 34 T at low temperature. The crossover field $H_{\rho,max}$ vanishes at 40 K and reaches 36 T at low temperature. Below 5 K the resistivity increases strongly with the magnetic field from 0 to 30 T. After a maximum at $H_{\rho,max}^{LT}$ (≈ 30 T) the resistivity decreases until 35 T. Above 35 T the "hidden-order" phase is destroyed and a cascade of first-order quantum phase transitions is induced at the fields H_1 , H_2 and H_3 , which are leading to a polarized paramagnetic state above 39 T. At 1.5 K, $\mu_0 H_1 = 35.1 \pm 0.1$ K, $\mu_0 H_2 = 37.4 \pm 0.1$ T for increasing field and 36.3 ± 0.1 T for decreasing field, and $\mu_0 H_3 = 39.0 \pm 0.1$ T are defined at the extrema of $\partial\rho_{xx}/\partial H$. Figure 1 (b) is the resulting H - T -phase diagram of URu₂Si₂ obtained from our magnetoresistivity data for $\mathbf{H} \parallel \mathbf{c}$.

Figure 1 (c) shows the resistivity ρ_{xx} of sample #1 as a function of the magnetic field when $\theta = (\mathbf{H}, \mathbf{c}) \approx 20^\circ$. The general form of the magnetoresistivity is similar to that obtained for $\mathbf{H} \parallel \mathbf{c}$ (Figure 1 (a)) showing the same transitions. The main difference is a shift of the resistivity curves to higher field values. For example the transition field H_1 , which is related to the destruction of the "hidden-order" phase at 1.5 K, is shifted from 35.1 T to 37.6 T. Figure 1 (d) is the resulting H - T -phase diagram of URu₂Si₂ obtained from our magnetoresistivity data for $(\mathbf{H}, \mathbf{c}) = 20^\circ$. Figure 2 shows that the phase diagram obtained for $(\mathbf{H} \parallel \mathbf{c}) = 20^\circ$ is re-scalable on the phase diagram obtained for $\mathbf{H} \parallel \mathbf{c}$, with a scaling factor of 0.94 which corresponds approximately to $\cos\theta$ with $\theta = 20^\circ$. This indicates that the physics of the whole H - T -phase diagram is mainly governed by the projection of the magnetic field along the \mathbf{c} -axis.

Figure 3 (a) shows the magnetoresistivity ρ_{xx} of sample #2 at $T = 1.5$ K as a function of the magnetic field, for different angles θ between the magnetic field \mathbf{H} and the \mathbf{c} -axis. As emphasized in [21], a strong sample-dependence of the magnetoresistivity at low temperature and below 35 T indicates that the signal is then controlled by an orbital effect. Here, the magnetoresistivity peaks at 30 T at $\approx 500\mu\Omega\cdot\text{cm}$ in sample #2 and at $\approx 300\mu\Omega\cdot\text{cm}$ in sample #1, this orbital signal being enhanced when the electronic mean-free path is higher, i.e., in sample #2 where the RRR is higher. When θ increases, the magnetoresistivity shifts to higher field values without significant change in the general form of $\rho_{xx}(H)$. The maximum of ρ_{xx} at $H_{\rho,max}^{LT}$ is slightly increasing, but the height of the plateau between H_2 and H_3 remains constant. The θ -dependance of the transition fields H_1 , H_2 , H_3 and the crossover field $H_{\rho,max}^{LT}$

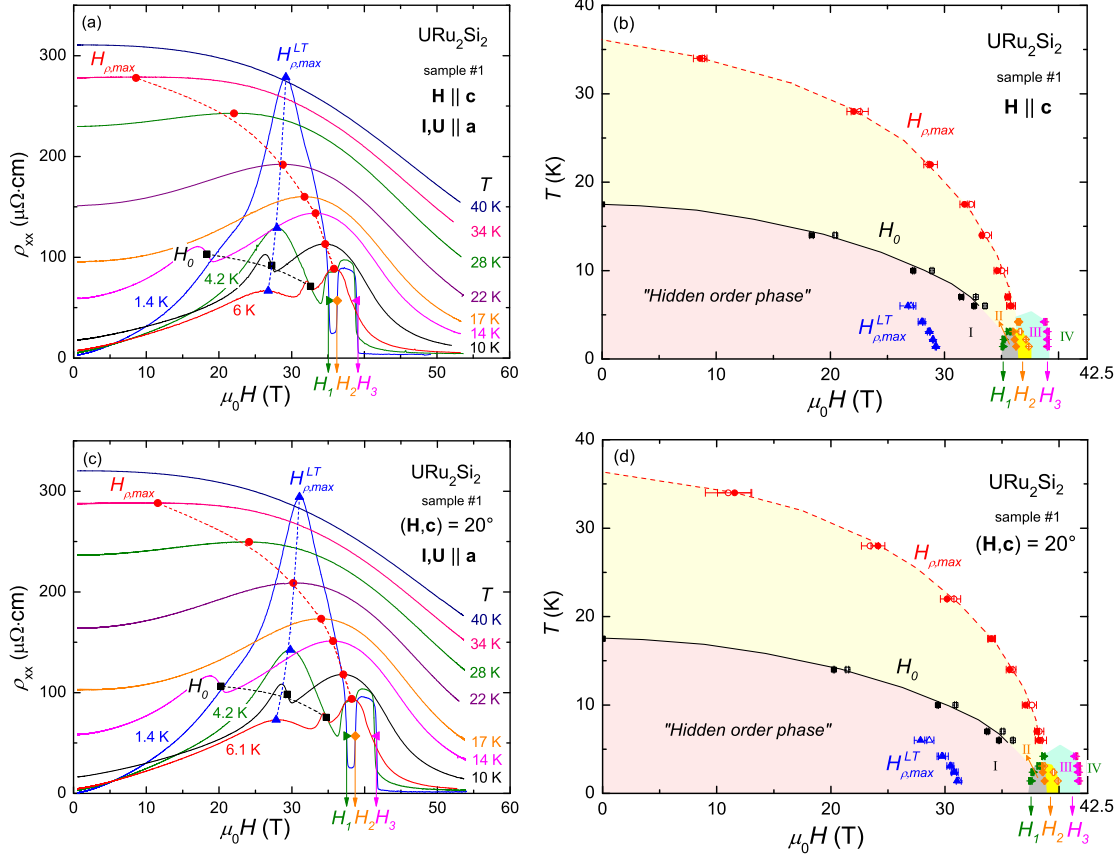


Fig. 1. Left: Resistivity ρ_{xx} as a function of the magnetic field H of sample #1 at temperatures from 1.4 K to 40 K, with (a) $\mathbf{H} \parallel \mathbf{c}$ and (c) $(\mathbf{H}, \mathbf{c}) = 20^\circ$. Symbols indicate the anomalies in the resistivity at the phase transition fields H_0 (black squares), H_1 (green triangles), H_2 (orange diamonds), and H_3 (magenta triangles), and crossover fields $H_{\rho,max}$ (red circles) and $H_{\rho,max}^{LT}$ (blue triangles). Dashed lines as guides to the eyes. Right: Resulting $H - T$ -phase diagrams for (b) $\mathbf{H} \parallel \mathbf{c}$ and (d) $(\mathbf{H}, \mathbf{c}) = 20^\circ$. Full symbols correspond to increasing field and open symbols to decreasing field. The lines are guides to the eyes.

is represented in Figure 3 (b). They all follow a $1/\cos\theta$ -law. This confirms that for θ up to 50° the physics of those transitions and crossover only depends on the projection of the magnetic field on the \mathbf{c} -axis.

4. Discussion

Our high-field magnetoresistivity measurements permitted to extend the study of the angle-dependence of the H - T -phase diagram of URu_2Si_2 to higher fields up to 60 T and higher temperatures up to 40 K (previous works [15,16] have been performed below 1.5 K and up to 45 T). We confirmed that, at low temperature and up to 60 T, all magnetic transition fields H_1 , H_2 and H_3 follow a $1/\cos\theta$ -law, i.e. for angles θ between \mathbf{H} and \mathbf{c} varying up to 50° . As well, we have shown here that, up to 17.5 K, the magnetic transition line H_0 related to the destruction of the hidden-order also follows a $1/\cos\theta$ -law, as well as the magnetic crossover $H_{\rho,max}$ which persists up to 40 K and which is associated to the development of intersite electronic correlations [21]. In addition, we have shown that the crossover field $H_{\rho,max}^{LT}$ at which the low-temperature magnetoresistivity is maximal also follows a $1/\cos\theta$ -

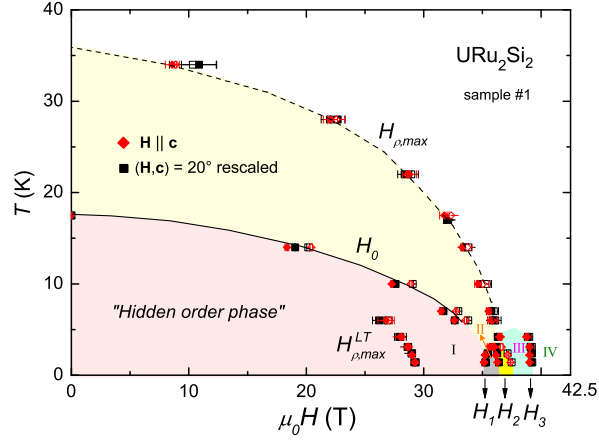


Fig. 2. H - T -phase diagram obtained for $(\mathbf{H}, \mathbf{c}) = \theta = 20^\circ$ (black squares), superposed with a scaling factor $0.94 = \cos\theta$ with the phase diagram obtained for $\mathbf{H} \parallel \mathbf{c}$ (red diamonds).

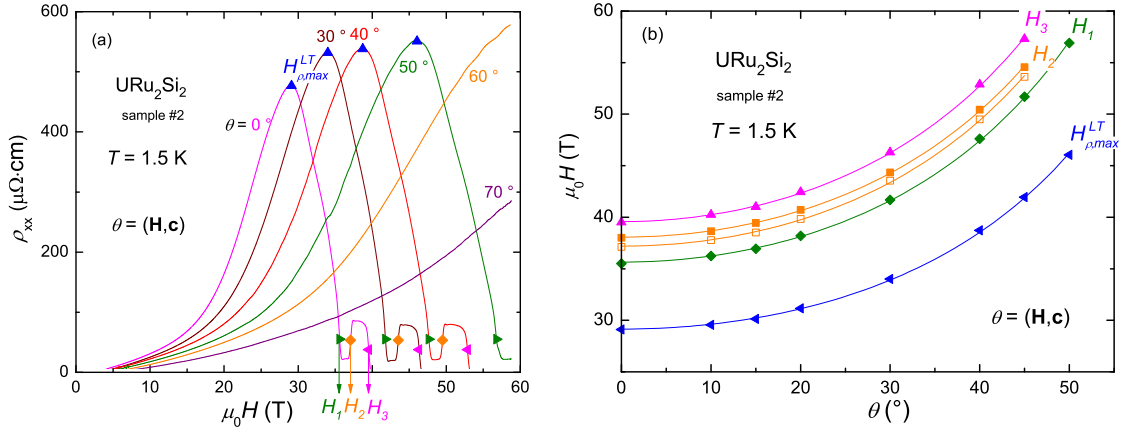


Fig. 3. a) Resistivity ρ_{xx} as a function of the magnetic field H of sample #2 at 1.5 K for different angles θ between the magnetic field \mathbf{H} and the \mathbf{c} -axis. Symbols indicate the transition fields H_1 (green triangles), H_2 (orange diamonds), H_3 (magenta triangles) and the crossover field $H_{\rho,max}^{LT}$ (blue triangles). By increasing θ the resistivity curves shift to higher field values with no change of their general form. For $\theta > 50^\circ$ the anomalies are shifted out of the field range [0-60 T]. b) Resulting H - θ -phase diagram made of the θ -dependence of H_1 , H_2 , H_3 and $H_{\rho,max}^{LT}$. The solid lines represent $1/\cos\theta$ -fits to the data.

law. In Ref. [21], this maximum has been related to a field-induced modification of the Fermi surface. The transition and crossover fields H_0 , H_1 , H_2 , H_3 , and $H_{\rho,max}$ related to the f -electron magnetic properties as well as the crossover field $H_{\rho,max}^{LT}$ related to a Fermi surface reconstruction are thus all controlled by the projection of the magnetic field along the c -axis, which is the easy magnetic axis of the system. This confirms that the magnetic properties of the $5f$ -electrons and that of the Fermi surface are intimately connected in URu_2Si_2 .

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